

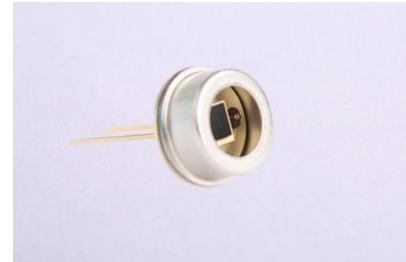


EUV photodiode

Model : ST-EUV6

General Features:

- SiC-based extreme ultraviolet (EUV) photodiode
- Excellent stability under high fluence EUV exposure
- Photovoltaic mode operation
- Visible blind and low dark current
- Windowless TO-39 metal housing
- High detection efficiency for 13.5 nm EUV radiation

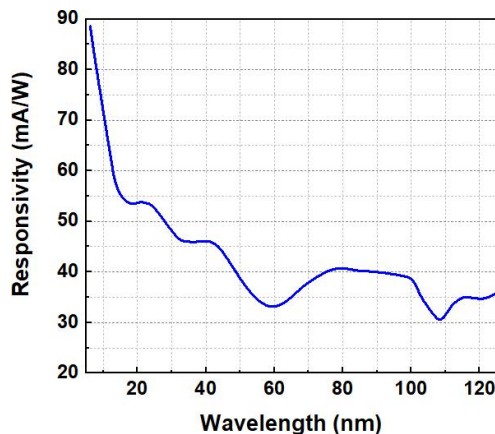


Applications: EUV radiation monitoring and flux measurement

Specifications:

Parameters	Symbol	Value	Unit
Maximum ratings			
Operation temperature range	T_{opt}	-20-80	°C
Storage temperature range	T_{sto}	-55-90	°C
Soldering temperature (3 s)	T_{sol}	260	°C
Maxium reverse voltage	V_{r-max}	-20	V
Electro-Optical characteristics (25 °C)			
Chip size	A	6.25	mm ²
Spectral response range	λ	5-125	nm
Responsivity (@ 13.5 nm)	R	58	mA/W
Dark current ($V_r = -5$ V)	I_d	< 10	pA
Capacitance (@ 0 V and 1 MHz)	C_p	175	pF
Rise Time ($V_r=0$ V, $R_L=50 \Omega$)	t_r	< 1	μ S

Spectral response



Package dimensions (unit: mm)

